



FS50KMJ-06F

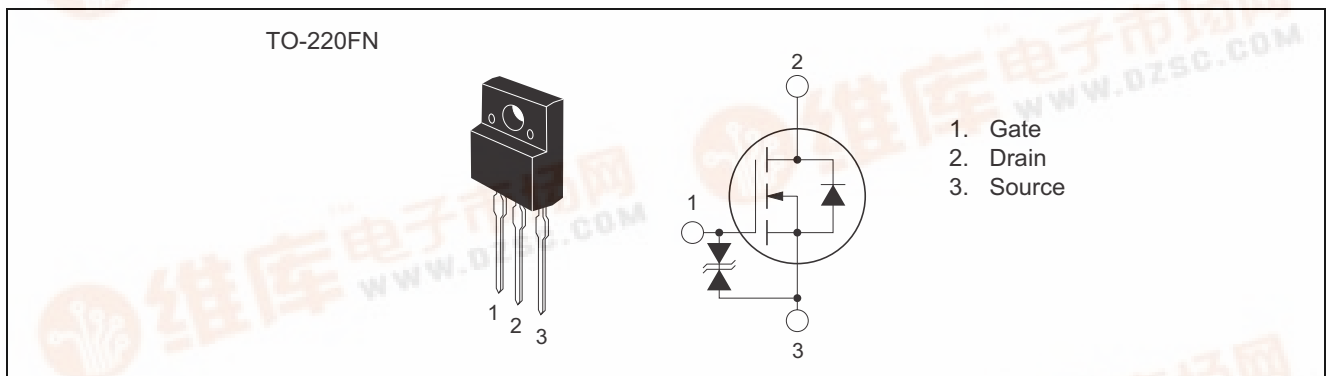
High-Speed Switching Use
Nch Power MOS FET

REJ03G0255-0100
Rev.1.00
Aug.20.2004

Features

- Drive voltage : 4 V
- V_{DSS} : 60 V
- $r_{DS(ON)(max)}$: 14 m Ω
- I_D : 50 A
- Recovery Time of the Integrated Fast Recovery Diode (TYP.) : 50 ns

Outline



Applications

Motor control, lamp control, solenoid control, DC-DC converters, etc.

Maximum Ratings

($T_c = 25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit	Conditions
Drain-source voltage	V_{DSS}	60	V	$V_{GS} = 0\text{ V}$
Gate-source voltage	V_{GSS}	± 20	V	$V_{DS} = 0\text{ V}$
Drain current	I_D	50	A	
Drain current (Pulsed)	I_{DM}	200	A	
Avalanche current (Pulsed)	I_{DA}	50	A	$L = 10\ \mu\text{H}$
Source current	I_S	50	A	
Source current (Pulsed)	I_{SM}	200	A	
Maximum power dissipation	P_D	25	W	
Channel temperature	T_{ch}	- 55 to +150	$^\circ\text{C}$	
Storage temperature	T_{stg}	- 55 to +150	$^\circ\text{C}$	
Isolation voltage	V_{iso}	2000	V	AC 1 minute, Terminal to case
Mass	—	2.0	g	Typical value

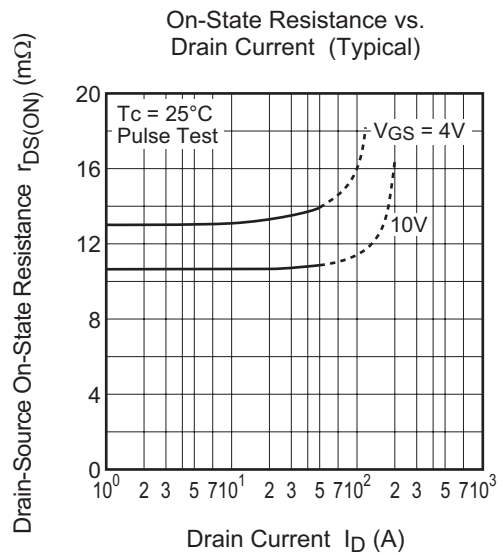
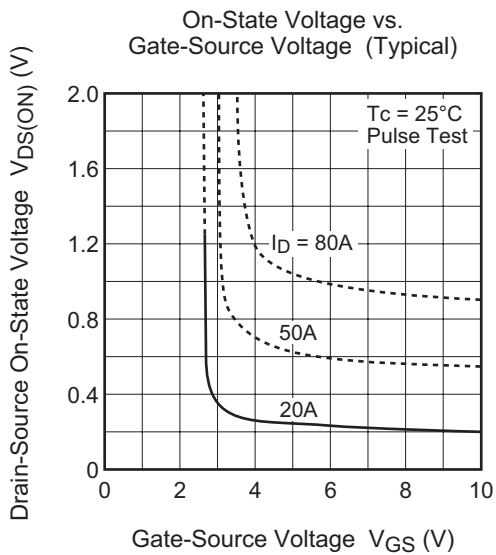
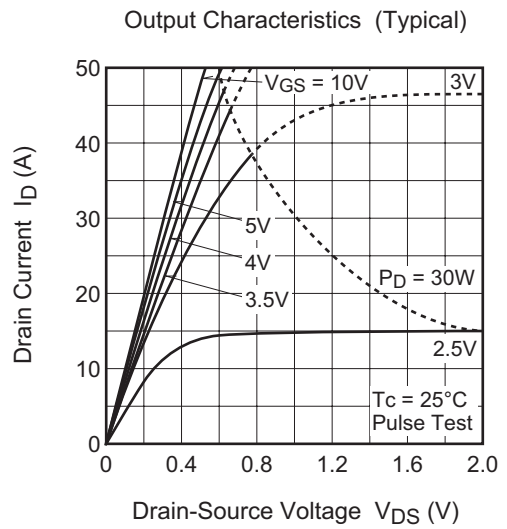
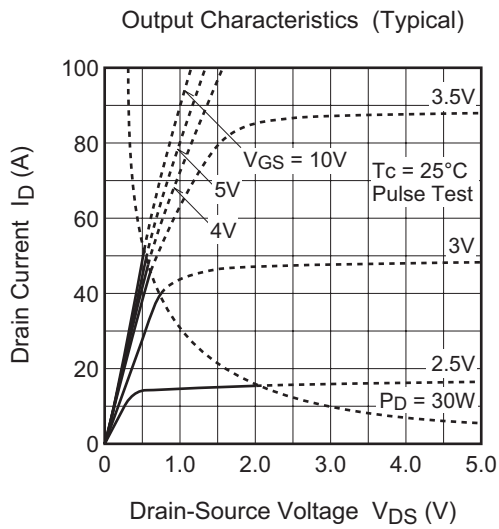
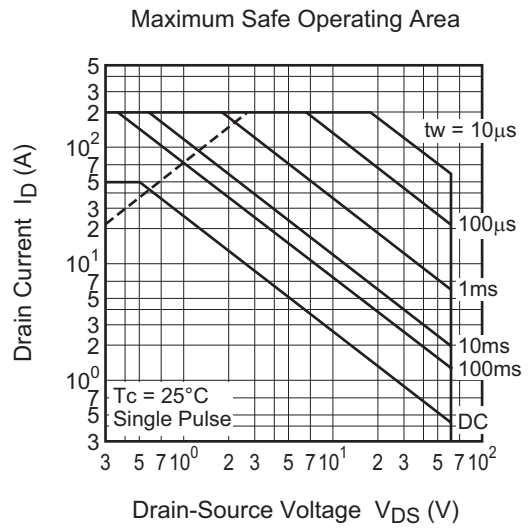
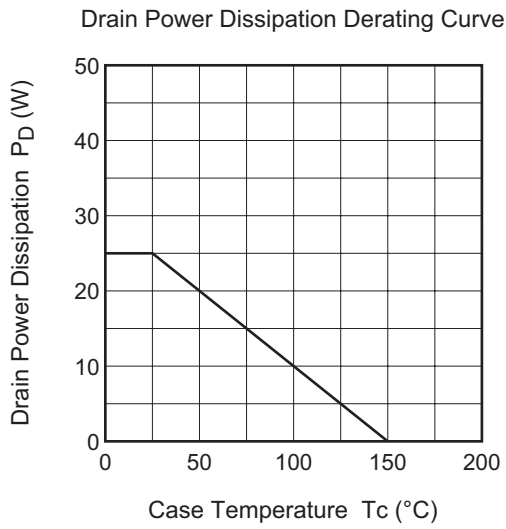


Electrical Characteristics

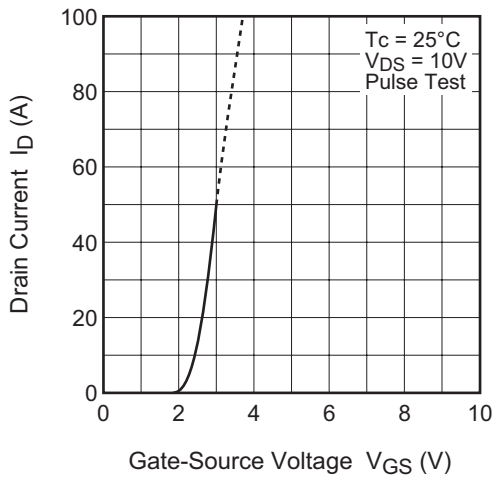
(Tch = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Drain-source breakdown voltage	$V_{(BR)DSS}$	60	—	—	V	$I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}$
Gate-source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}, V_{DS} = 0 \text{ V}$
Drain-source leakage current	I_{DSS}	—	—	100	μA	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$
Gate-source leakage current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$
Gate-source threshold voltage	$V_{GS(th)}$	1.0	1.5	2.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Drain-source on-state resistance	$r_{DS(ON)}$	—	12	14	m Ω	$I_D = 25 \text{ A}, V_{GS} = 10 \text{ V}$
Drain-source on-state resistance	$r_{DS(ON)}$	—	14	18	m Ω	$I_D = 25 \text{ A}, V_{GS} = 4 \text{ V}$
Drain-source on-state voltage	$V_{DS(ON)}$	—	0.30	0.35	V	$I_D = 25 \text{ A}, V_{GS} = 10 \text{ V}$
Forward transfer admittance	$ y_{fs} $	—	60	—	S	$I_D = 25 \text{ A}, V_{DS} = 10 \text{ V}$
Input capacitance	C_{iss}	—	3850	—	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1\text{MHz}$
Output capacitance	C_{oss}	—	580	—	pF	
Reverse transfer capacitance	C_{rss}	—	320	—	pF	
Turn-on delay time	$t_{d(on)}$	—	19	—	ns	$V_{DD} = 30 \text{ V}, I_D = 25 \text{ A},$ $V_{GS} = 10 \text{ V},$ $R_{GEN} = R_{GS} = 50 \text{ }\Omega$
Rise time	t_r	—	70	—	ns	
Turn-off delay time	$t_{d(off)}$	—	360	—	ns	
Fall time	t_f	—	160	—	ns	
Source-drain voltage	V_{SD}	—	1.0	1.5	V	$I_S = 25 \text{ A}, V_{GS} = 0 \text{ V}$
Thermal resistance	$R_{th(ch-c)}$	—	—	5.0	$^{\circ}\text{C/W}$	Channel to case
Reverse recovery time	t_{rr}	—	50	—	ns	$I_S = 50 \text{ A}, \text{dis}/\text{dt} = -100 \text{ A}/\mu\text{s}$

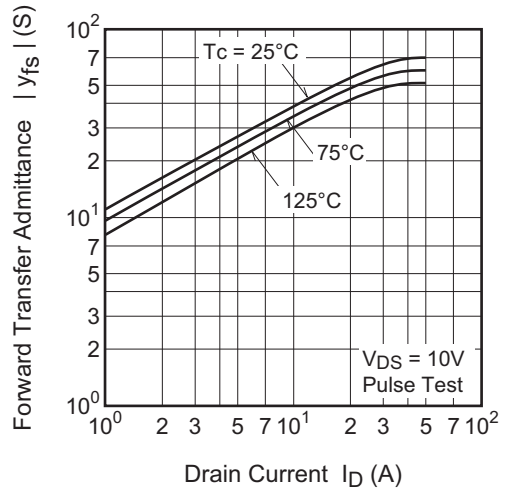
Performance Curves



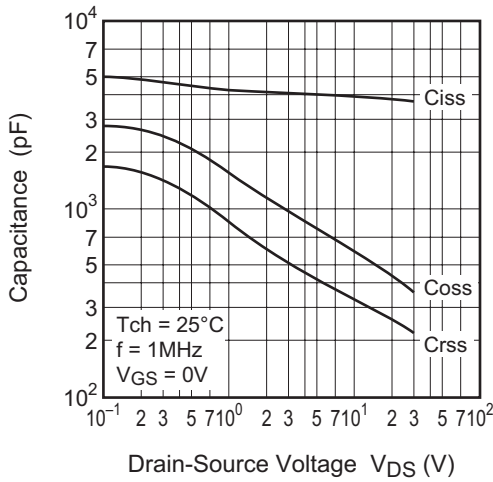
Transfer Characteristics (Typical)



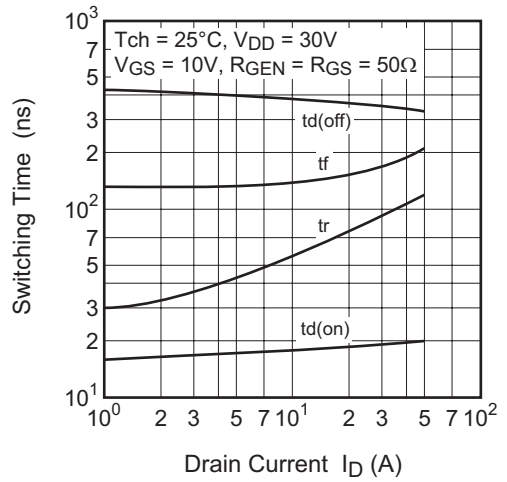
Forward Transfer Admittance vs. Drain Current (Typical)



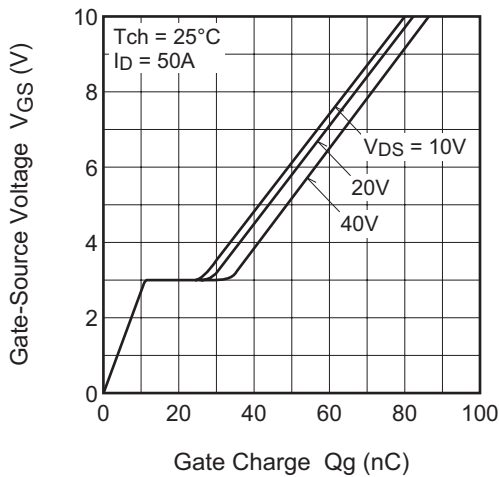
Capacitance vs. Drain-Source Voltage (Typical)



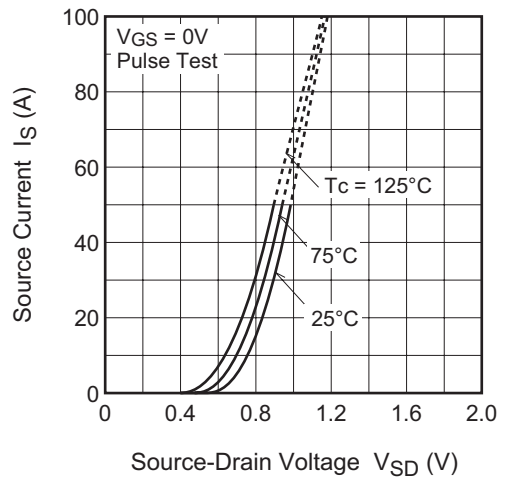
Switching Characteristics (Typical)

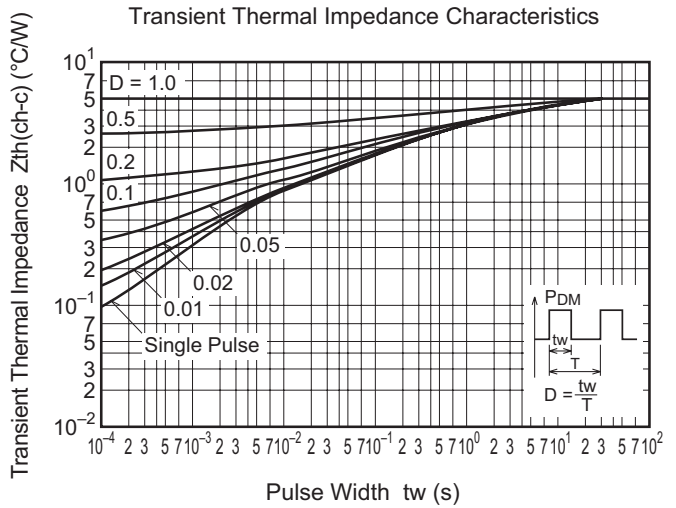
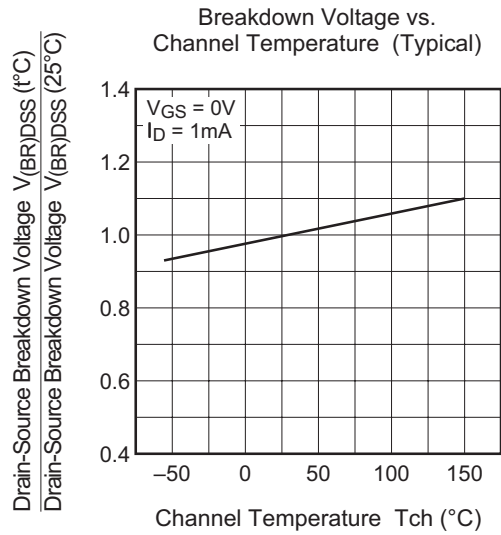
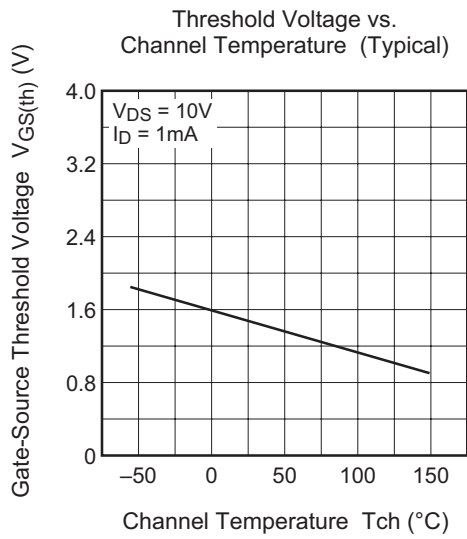
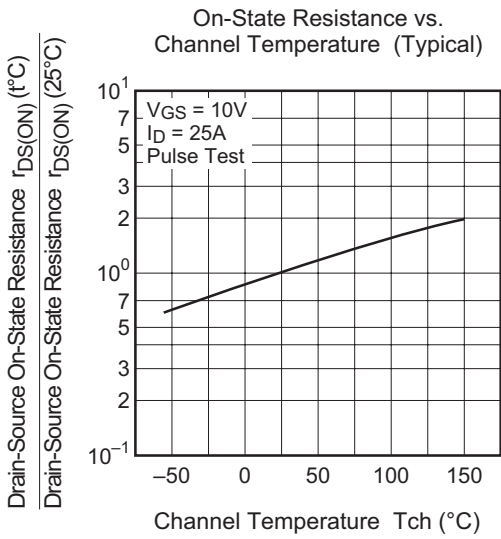


Gate-Source Voltage vs. Gate Charge (Typical)

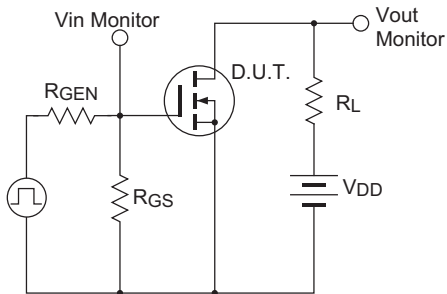


Source-Drain Diode Forward Characteristics (Typical)

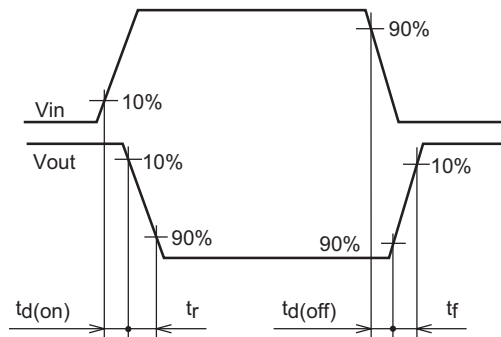




Switching Time Measurement Circuit



Switching Waveform



Package Dimensions

TO-220FN

EIAJ Package Code	JEDEC Code	Mass (g) (reference value)	Lead Material
—	—	2.0	Cu alloy

Technical drawings showing dimensions for the TO-220FN package:

- Top view: Overall width 10 ± 0.3 mm, mounting hole diameter $\phi 3.2 \pm 0.2$ mm, distance from hole to lead center 3 ± 0.3 mm, distance from hole to lead edge 6.5 ± 0.3 mm, lead spacing 1.1 ± 0.2 mm, lead thickness 0.75 ± 0.15 mm, lead length 1.1 ± 0.2 mm, distance from lead edge to lead center 3.6 ± 0.3 mm, distance from lead edge to lead tip 14 ± 0.5 mm, distance from lead edge to lead base 2.54 ± 0.25 mm.
- Side view: Lead height 2.8 ± 0.2 mm, lead thickness 0.75 ± 0.15 mm.
- Lead view: Lead length 4.5 ± 0.2 mm, lead thickness 2.6 ± 0.2 mm.

Note 1) The dimensional figures indicate representative values unless otherwise the tolerance is specified.

Symbol	Dimension in Millimeters		
	Min	Typ	Max
A	—	—	—
A ₁	—	—	—
A ₂	—	—	—
b	—	—	—
D	—	—	—
E	—	—	—
e	—	—	—
x	—	—	—
y	—	—	—
y ₁	—	—	—
ZD	—	—	—
ZE	—	—	—

Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Plastic Magazine (Tube)	50	Type name	FS50KMJ-06F
Lead form	Plastic Magazine (Tube)	50	Type name – Lead forming code	FS50KMJ-06F-A8

Note : Please confirm the specification about the shipping in detail.

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